

Appl. No.
Filed

APR 19 2002

09/737,439
December 13, 2000

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ORIGINALLY FILED

IN THE CLAIMS:

Please amend Claims 1-4 and 8 as follows:

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APR 23 2002
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- a¹
1. An integrated circuit inductor, the integrated circuit having a silicon substrate and an oxide layer on the silicon substrate, the inductor comprising:
 - an inductive loop deposited on the oxide layer;
 - a plurality of apertures in the oxide layer beneath the inductive loop;
 - a plurality of bridges adjacent the apertures and provided by portions of the oxide layer between an inner region and an outer region of the oxide layer, respectively within and without the inductive loop, the loop being supported on the bridges; and
 - a trench formed in the silicon substrate beneath the bridges, to provide an air gap between the inductive loop and the silicon substrate.
 2. The integrated circuit inductor as claimed in Claim 1, wherein the apertures and the bridges extend generally radially from the inner region.
 3. The integrated circuit inductor as claimed in Claim 1, wherein the trench extends circumferentially around the inner region.
 4. The integrated circuit inductor as claimed in Claim 2, wherein the trench extends circumferentially around the inner region.
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- a²
8. The integrated circuit inductor as claimed in Claim 1, wherein the oxide layer includes an underpass connection in one of the bridges from a peripheral connection to another end of the inductor to its inner end.

Please add the following Claim 13:

- a³
13. An integrated circuit inductor, the integrated circuit having a silicon substrate and an oxide layer on the silicon substrate, the inductor comprising:
 - an inductive loop deposited on the oxide layer;
 - a plurality of apertures in the oxide layer beneath the inductive loop, each aperture forming an underpass to a plurality of segments of the inductive loop;
 - a plurality of bridges adjacent the apertures and provided by portions of the oxide layer between an inner region and an outer region of the oxide layer, respectively within and without the inductive loop, the loop being supported on the bridges; and